

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 1-72, and add new claims 76-99 as follows:

Listing of Claims:

Claims 1-72 (Cancelled)

73. (Original) An in-process device, comprising:
a substrate; and
a conductive layer over said substrate and having a surface stuffed with a non-oxygen material.
74. (Original) The in-process device of claim 73, wherein said surface is a nitrogen-stuffed surface.
75. (Original) The device in claim 74, wherein said surface is contacting an oxygen molecule.
76. (New) The in-process device of claim 73 wherein the carbon-silicon compound is selected from the group consisting of methylsilane, hexamethyldisilane and hexamethyldisilazane.
77. (New) The in-process device of claim 75 wherein the other conductive layer comprises copper.
78. (New) The in-process device of claim 73 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

79. (New) The in-process device of claim 78 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

80. (New) The in-process device of claim 73 wherein the substrate comprises a silicon substrate.

81. (New) An in-process device, comprising:
a substrate; and
a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associate with oxygen by being exposed to a material selected from the group consisting of phosphine and methylsilane.

82. (New) The in-process device of claim 81 wherein the conductive layer comprises tungsten nitride.

83. (New) The in-process device of claim 82 further comprising another conductive layer formed on the tungsten nitride layer.

84. (New) The in-process device of claim 83 wherein the other conductive layer comprises copper.

85. (New) The in-process device of claim 81 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

86. (New) The in-process device of claim 85 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

87. (New) The in-process device of claim 81 wherein the substrate comprises a silicon substrate.

88. (New) An in-process device, comprising:
a substrate; and
a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associate with oxygen by being exposed to methylsilane.

89. (New) The in-process device of claim 88 wherein the conductive layer comprises tungsten nitride.

90. (New) The in-process device of claim 89 further comprising another conductive layer formed on the tungsten nitride layer.

91. (New) The in-process device of claim 90 wherein the other conductive layer comprises copper.

92. (New) The in-process device of claim 88 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

93. (New) The in-process device of claim 92 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

94. (New) The in-process device of claim 88 wherein the substrate comprises a silicon substrate.

95. (New) An in-process device, comprising:
a substrate;

a conductive layer disposed on the substrate and exposed to an oxygen-inhibiting material selected from the group consisting of phosphine and methylsilane;

a first conductive layer disposed on the metal layer; and

a second conductive layer disposed on the first conductive layer.

96. (New) The in-process device of claim 95 wherein the conductive layer comprises tungsten nitride.

97. (New) The in-process device of claim 96, comprising another conductive layer disposed on the tungsten nitride layer.

98. (New) The in-process device of claim 97 wherein the another conductive layer comprises copper.

99. (New) The in-process device of claim 95 wherein the substrate comprises a silicon substrate.